

N-Channel Logic Level Enhancement Mode Field Effect Transistor

BSS138K

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Green Compound
- ESD HBM = 2000 V as per JEDEC A114A;
ESD CDM = 2000 V as per JEDEC C101C
- This Device is Pb-Free and is RoHS Compliant

ABSOLUTE MAXIMUM RATINGS

($T_A = 25^\circ\text{C}$ unless otherwise noted) (Note 1)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	50	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current – Continuous	0.22	A
	Drain Current – Pulsed	0.88	
P_D	Total Device Dissipation	350	mW
	Derating above $T_A = 25^\circ\text{C}$	2.8	mW/ $^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to $+150$	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to $+150$	$^\circ\text{C}$

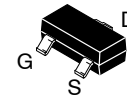
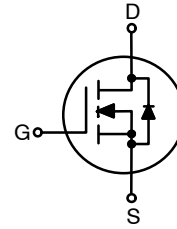
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. These ratings are limiting values above which the serviceability of any semiconductor device maybe impaired.

THERMAL CHARACTERISTICS

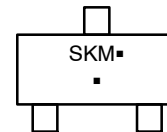
Symbol	Parameter	Value	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	350	$^\circ\text{C/W}$

2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.



SOT-23-3
CASE 318-08

MARKING DIAGRAM



SK = Specific Device Code
M = Assembly Operation Month
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BSS138K	SOT-23-3 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

BSS138K

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
--------	-----------	-----------------	-----	-----	-----	------

OFF CHARACTERISTICS

BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 10\text{ }\mu\text{A}$	50	–	–	V
$\frac{BV_{DSS}}{T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	–	0.11	–	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$	–	–	0.1	μA
I_{GSS}	Gate–Body Leakage	$V_{GS} = \pm 12\text{ V}, V_{DS} = 0\text{ V}$	–	–	± 1	μA
		$V_{GS} = \pm 10\text{ V}, V_{DS} = 0\text{ V}$	–	–	± 0.5	
		$V_{GS} = \pm 5\text{ V}, V_{DS} = 0\text{ V}$	–	–	± 0.05	

ON CHARACTERISTICS

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.6	–	1.2	V
$\frac{V_{GS(th)}}{T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 1\text{ mA}$, Referenced to 25°C	–	–1.4	–	mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 1.8\text{ V}, I_D = 50\text{ mA}$	–	–	2.5	Ω
		$V_{GS} = 2.5\text{ V}, I_D = 50\text{ mA}$	–	–	2.0	
		$V_{GS} = 5\text{ V}, I_D = 50\text{ mA}$	–	–	1.6	
$I_{D(ON)}$	On–State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	0.2	–	–	A
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 200\text{ mA}$	200	–	–	mS

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	–	58	–	pF
C_{oss}	Output Capacitance		–	9.75	–	
C_{rss}	Reverse Transfer Capacitance		–	5.2	–	
R_G	Gate Resistance	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ mV}$	–	281	–	Ω

SWITCHING CHARACTERISTICS

$t_{D(ON)}$	Turn–On Delay Time	$V_{DD} = 30\text{ V}, I_D = 0.29\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$	–	–	5	ns
t_r	Turn–On Rise Time		–	–	5	
$t_{D(OFF)}$	Turn–Off Delay Time		–	–	60	
t_f	Turn–Off Fall Time		–	–	35	
Q_g	Total Gate Charge	$V_{DS} = 25\text{ V}, I_D = 0.2\text{ A},$ $V_{GS} = 10\text{ V}, I_G = 0.1\text{ mA}$	–	–	2.4	nC
Q_{gs}	Gate–Source Charge		–	–	0.5	
Q_{gd}	Gate–Drain Charge		–	–	0.5	

DRAIN–SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

V_{sd}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 115\text{ mA}$	–	–	1.2	V
----------	------------------------------------	--	---	---	-----	---

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

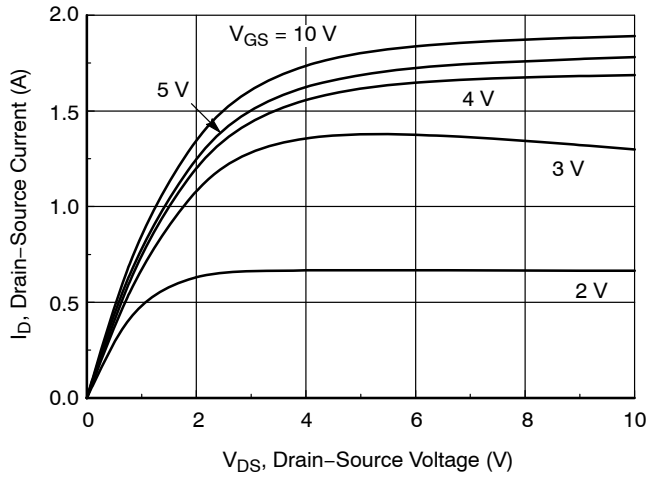


Figure 1. On-Region Characteristics

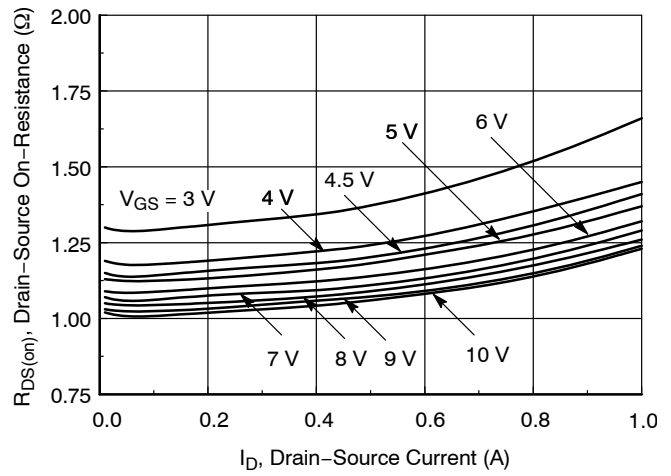


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

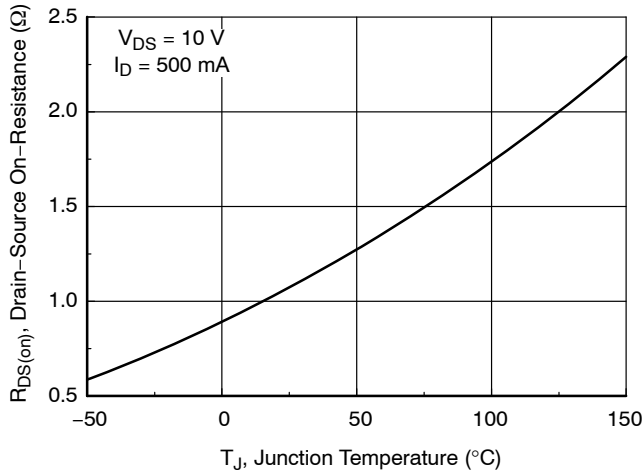


Figure 3. On-Resistance Variation with Temperature

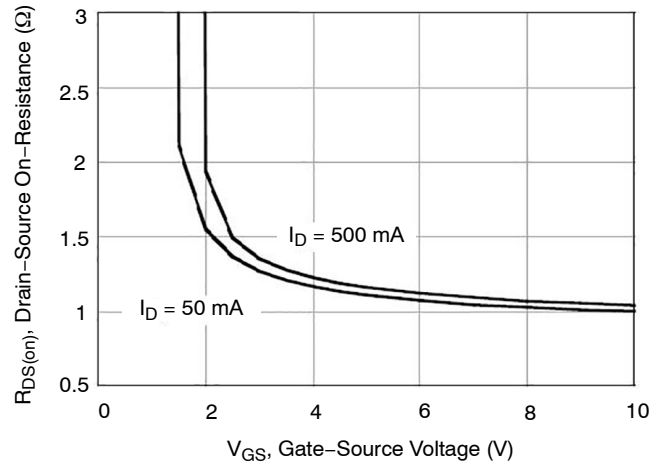


Figure 4. On-Resistance Variation with Gate-Source Voltage

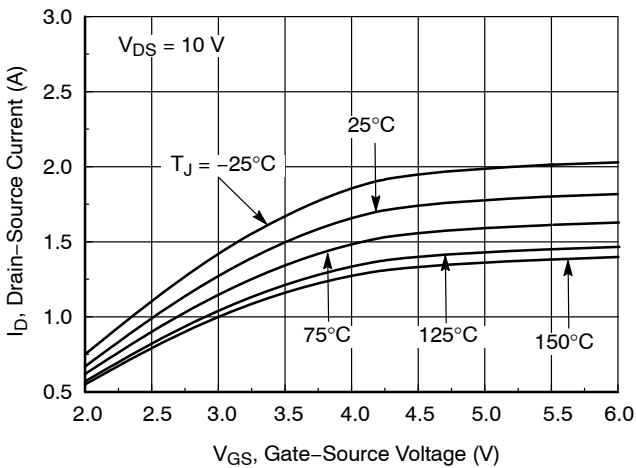


Figure 5. Transfer Characteristics

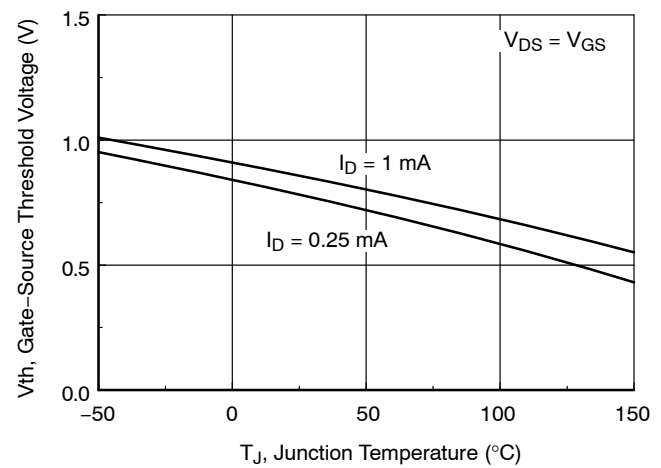


Figure 6. Gate Threshold Variation with Temperature

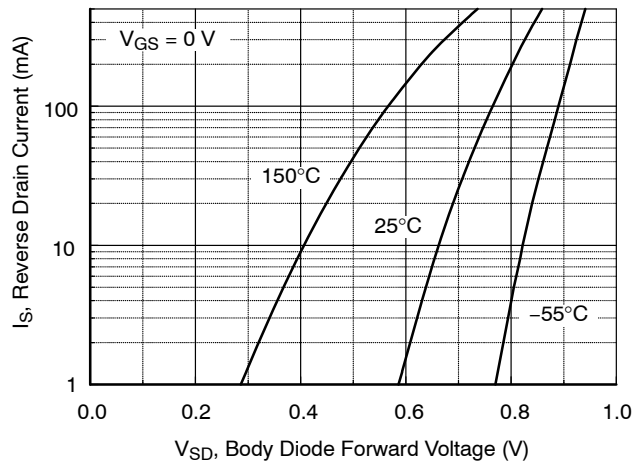
TYPICAL CHARACTERISTICS (continued)

Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales